# **2SB0789, 2SB0789A** (2SB789, 2SB789A)

### Silicon PNP epitaxial planar type

For low-frequency driver amplification

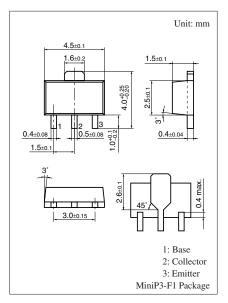
#### ■ Features

- High collector-emitter voltage (Base open) V<sub>CEO</sub>
- Large collector power dissipation P<sub>C</sub>

#### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage	2SB0789	V <sub>CBO</sub>	-100	V
(Emitter open)	2SB0789A		-120	
Collector-emitter voltage	2SB0789	V <sub>CEO</sub>	-100	V
(Base open)	2SB0789A		-120	
Emitter-base voltage (Coll	$V_{EBO}$	-5	V	
Collector current	$I_C$	- 0.5	A	
Peak collector current	$I_{CP}$	-1	A	
Collector power dissipation	$P_{C}$	1	W	
Junction temperature	$T_{j}$	150	°C	
Storage temperature	$T_{stg}$	-55 to +150	°C	

Note) \*: Print circuit board: Copper foil area of  $1~\rm cm^2$  or more, and the board thickness of  $1.7~\rm mm$  for the collector portion.



Marking Symbol:

• 2SB0789: D • 2SB0789A: E

#### ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage	2SB0789	V <sub>CEO</sub>	$I_C = -100 \ \mu A, I_B = 0$	-100			V
(Base open)	2SB0789A			-120			
Emitter-base voltage (Colle	ctor open)	V <sub>EBO</sub>	$I_E = -10 \ \mu A, I_C = 0$	-5			V
Forward current transfer ratio *1		h <sub>FE1</sub> *2	$V_{CE} = -10 \text{ V}, I_{C} = -150 \text{ mA}$	90		220	_
		h <sub>FE2</sub>	$V_{CE} = -5 \text{ V}, I_C = -500 \text{ mA}$	50			
Collector-emitter saturation	voltage *1	V <sub>CE(sat)</sub>	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		- 0.2	- 0.6	V
Base-emitter saturation volt	age *1	V <sub>BE(sat)</sub>	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		- 0.85	-1.20	V
Transition frequency		$f_T$	$V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		120		MHz
Collector output capacitance		C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$			30	pF
(Common base, input open	circuited)						

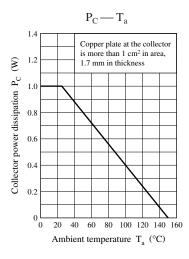
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

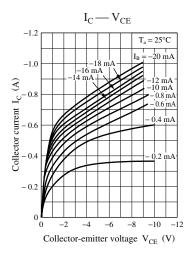
2. \*1: Pulse measurement

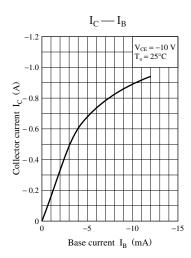
\*2: Rank classification

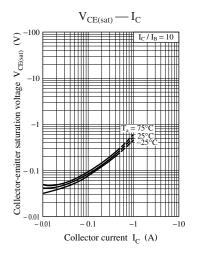
Rank	Q	R		
h <sub>FE1</sub>	90 to 155	130 to 220		

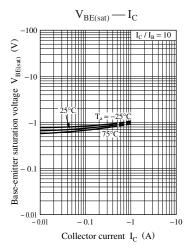
Note) The part number in the parenthesis shows conventional part number.

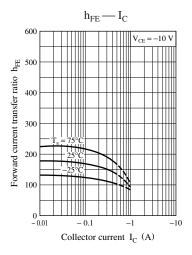


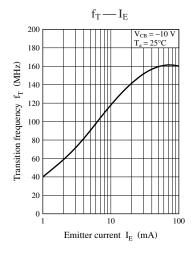


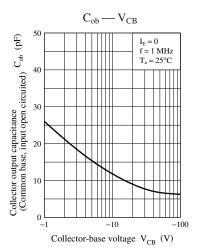












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